



NTE6240 & NTE6244 Silicon Rectifier Super Fast, Dual, Center Tap

Features:

- Dual Rectifier Construction:
 - NTE6240— Positive Center-Tap
 - NTE6244— Negative Center-Tap
- Superfast Recovery Times, High Voltage
- Low Power Loss, High Efficiency
- Low Forward Voltage, High Current Capability
- High Temperature Soldering Guaranteed: +250°C @ .250" (6.35mm) from Case for 10sec

Applications:

- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Maximum Ratings and Electrical Characteristics: ($T_A = +25^\circ\text{C}$, resistive or inductive load, for capacitive load, derate current by 20%, unless otherwise specified)	
Maximum Recurrent Peak Reverse Voltage, V_{RRM}	200V
Maximum RMS Voltage, V_{RMS}	140V
Maximum DC Blocking Voltage, V_{DC}	200V
Maximum Average Forward Rectified Current (.375 (9.5) Lead Lengths at $+100^\circ\text{C}$), $I_{(AV)}$	16A
Peak Forward Surge Current, I_{FSM} 8.3ms single half sine-wave superimposed on rated load	100A
Maximum Instantaneous Forward Voltage (Per Diode, $I_F = 8\text{A}$), V_F	975mV
Maximum DC Reverse Current ($V_{DC} = 200\text{V}$), I_R $T_A = +25^\circ\text{C}$	5μA
$T_A = +100^\circ\text{C}$	50μA
Maximum Reverse Recovery Time ($T_J = +25^\circ\text{C}$, Note 1), t_{rr}	35ns
Typical Thermal Resistance, Junction-to-Case, R_{thJC}	5.5°C/W
Operating Junction Temperature Range, T_J	-65° to +150°C
Storage Temperature Range, T_{stg}	-65° to +150°C

Note 1. Reverse Recovery Test Conditions: $I_F = 5\text{A}$, $I_R = 1\text{A}$, $I_{RR} = 25\text{A}$

Note 2. Measured at 1MHz and applied reverse voltage of 4V.

